

isc Silicon PNP Power Transistor

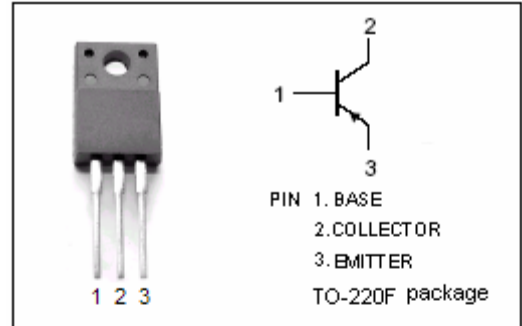
2SB1562

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 300 \sim 1000 @ (V_{CE} = -5V, I_C = -0.5A)$
- Low Saturation Voltage-
: $V_{CE(sat)} = -0.5V(TYP.) @ (I_C = -2A, I_B = -20mA)$

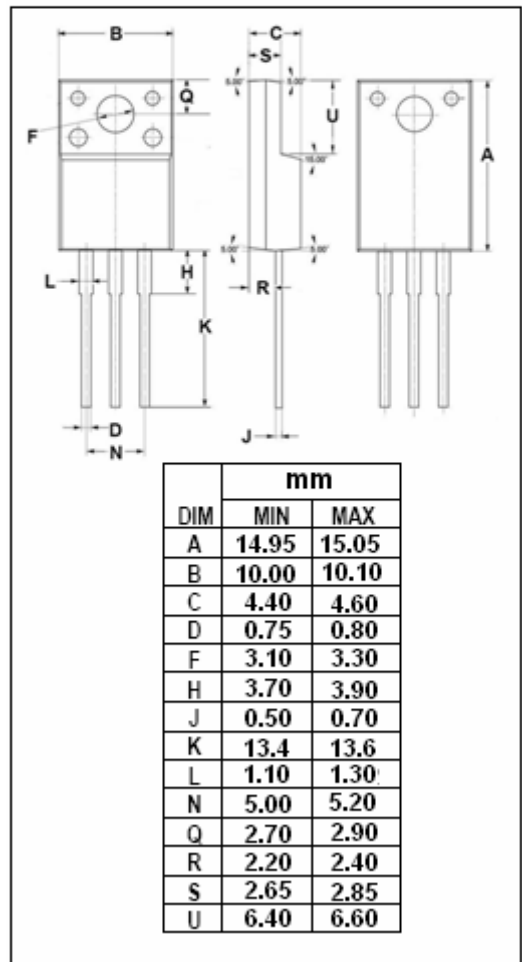
APPLICATIONS

- Designed for power amplifier applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Pulse	-6	A
I_B	Base Current-Continuous	-0.6	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	25	W
	Collector Power Dissipation @ $T_a=25^{\circ}C$	2	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB1562****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA ; I _B = 0	-60			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -20mA		-0.5	-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A ; V _{CE} = -5V		-0.7	-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V ; I _E =0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C =0			-100	μ A
h _{FE-1}	DC Current Gain	I _C = -0.5A ; V _{CE} = -5V	300		1000	
h _{FE-2}	DC Current Gain	I _C = -2A ; V _{CE} = -5V	100			
C _{OB}	Output Capacitance	I _E =0 ; V _{CB} = -10V; f _{test} = 1.0MHz		60		pF